

isc N-Channel MOSFET Transistor IPD90R1K2C3,IIPD90R1K2C3

• FEATURES

- Static drain-source on-resistance: Ros(on)≤1.2 Ω
- Enhancement mode:
- · 100% avalanche tested
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

High peak current capability



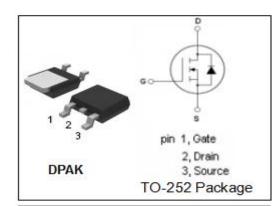
• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

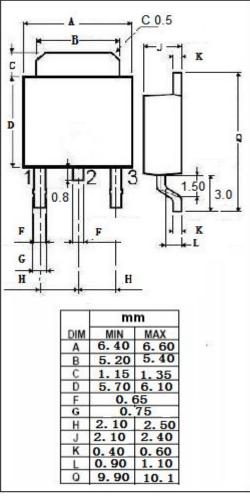
| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|---------|--------------|
| V _{DSS} | Drain-Source Voltage | 900 | V |
| V _{GS} | Gate-Source Voltage | ±20 | V |
| I _D | Drain Current-Continuous | 5.1 | Α |
| I_{DM} | Drain Current-Single Pulsed | 10 | A |
| P _D | Total Dissipation @T _C =25°C 83 | | W |
| Tj | Max. Operating Junction Temperature | 150 | $^{\circ}$ C |
| T _{stg} | Storage Temperature | -55~150 | $^{\circ}$ |

• THERMAL CHARACTERISTICS

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| SYMBOL | PARAMETER | MAX | UNIT | |
|----------|---------------------------------------|-----|------|--|
| Rth(j-c) | Channel-to-case thermal resistance | 1.5 | °C/W | |
| Rth(j-a) | Channel-to-ambient thermal resistance | 62 | °C/W | |







isc N-Channel MOSFET Transistor

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | MAX | UNIT |
|---------------------|--------------------------------|---|-----|-----|-----|------------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D =0.25mA | 900 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} ; I _D =0.31mA | 2.5 | | 3.5 | V |
| $R_{DS(on)}$ | Drain-Source On-Resistance | V _{GS} =10V; I _D =2.8A | | | 1.2 | Ω |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =20V; V _{DS} =0V | | | 0.1 | μ А |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =900V; V _{GS} = 0V | | | 1 | μА |
| V_{SD} | Diode forward voltage | I _F =2.8A, V _{GS} = 0V | | | 1.2 | V |

NOTICE:

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